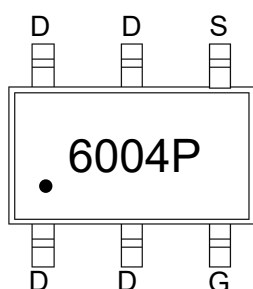


Features

- High density cell design for ultra low $R_{DS(on)}$
- Fully characterized avalanche voltage and current
- Excellent package for good heat dissipation

Application

- PWM applications
- Power management
- Load switch

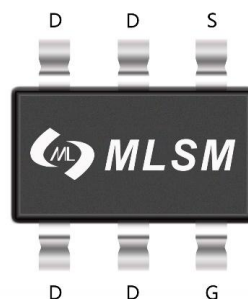


6004P: Device code

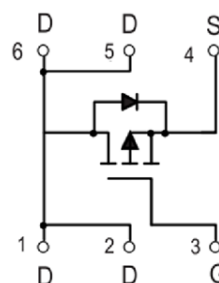
Marking and pin assignment

Product Summary

V_{DS}	$R_{DS(ON)}$ TYP	I_D
-60V	110m Ω @-10V	-4A
	150m Ω @-4.5V	



SOT-23-6L top view



Schematic diagram



Pb-Free



Halogen-Free

Absolute Maximum Ratings (TA=25°C unless otherwise noted)

Symbol	Parameter	Rating	Unit
Common Ratings (TC=25°C Unless Otherwise Noted)			
V_{DS}	Drain-Source Breakdown Voltage	-60	V
V_{GS}	Gate-Source Voltage	± 20	V
T_J	Maximum Junction Temperature	150	°C
T_{STG}	Storage Temperature Range	-55 to 150	°C
I_S	Diode Continuous Forward Current	$T_C=25^\circ\text{C}$ -4.0	A

Mounted on Large Heat Sink

I_{DM}	Pulse Drain Current Tested	$T_C=25^\circ\text{C}$ -16	A
I_D	Continuous Drain Current	$T_C=25^\circ\text{C}$ -4.0	A
P_D	Maximum Power Dissipation	$T_C=25^\circ\text{C}$ -1.5	W
$R_{\theta JA}$	Thermal Resistance Junction-to-Ambient	113	°C/W

Ordering Information (Example)

Type	Package	Marking	Minimum Package(pcs)	Inner Box Quantity(pcs)	Outer Carton Quantity(pcs)	Delivery Mode
MLSL6004P	SOT-23-6L	6004P	3,000	45,000	180,000	7" reel

Electrical Characteristics (T _J =25℃ unless otherwise noted)						
Symbol	Parameter	Condition	Min	Typ	Max	Unit
Static Electrical Characteristics @ T _J = 25℃ (unless otherwise stated)						
BV _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =-250μA	-60	--	--	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =-60V, V _{GS} =0V	--	--	-1.0	μA
I _{GSS}	Gate-Body Leakage Current	V _{GS} =±20V, V _{DS} =0V	--	--	±100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =-250μA	-1.0	-1.8	-2.5	V
R _{DS(on)}	Drain-Source On-State Resistance	V _{GS} =-10V, I _D =-4A	--	110	150	mΩ
		V _{GS} =-4.5V, I _D =-2A	--	150	200	mΩ
Dynamic Electrical Characteristics @ T _J = 25℃ (unless otherwise stated)						
C _{ISS}	Input Capacitance	V _{DS} =-15V, V _{GS} =0V, f=1MHz	--	715	--	pF
C _{OSS}	Output Capacitance		--	51	--	pF
C _{RSS}	Reverse Transfer Capacitance		--	34	--	pF
Switching Characteristics						
Q _g	Total Gate Charge	V _{DS} =-20V, I _D =-2A, V _{GS} =-4.5V	--	6	--	nC
Q _{gs}	Gate Source Charge		--	3	--	nC
Q _{gd}	Gate Drain Charge		--	2	--	nC
t _{d(on)}	Turn-on Delay Time	V _{DD} =-12V, I _D =-1A, V _{GS} =-10V, R _G =3.3Ω	--	10	--	nS
t _r	Turn-on Rise Time		--	17	--	nS
t _{d(off)}	Turn-Off Delay Time		--	22	--	nS
t _f	Turn-Off Fall Time		--	21	--	nS
Source- Drain Diode Characteristics						
V _{SD}	Forward on voltage	T _J =25℃, I _S =-4A	--	--	-1.2	V

Typical Operating Characteristics

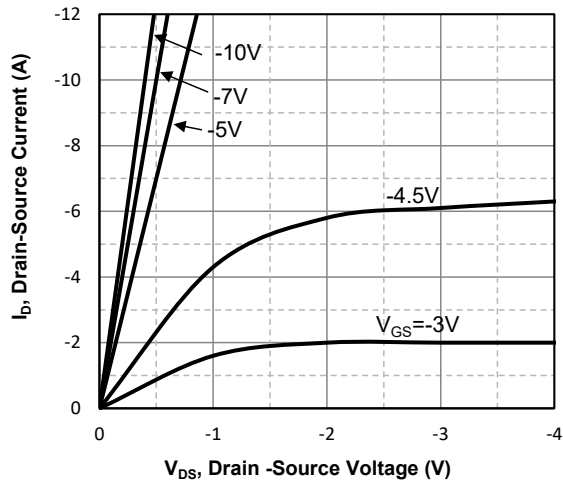


Fig1. Typical Output Characteristics

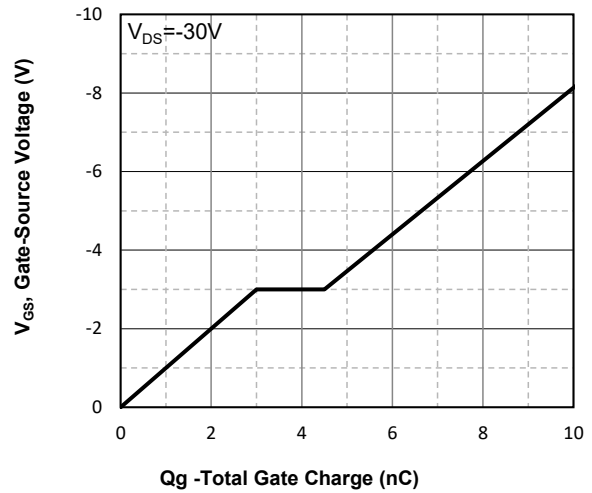


Fig2. Typical Gate Charge Vs. Gate-Source Voltage

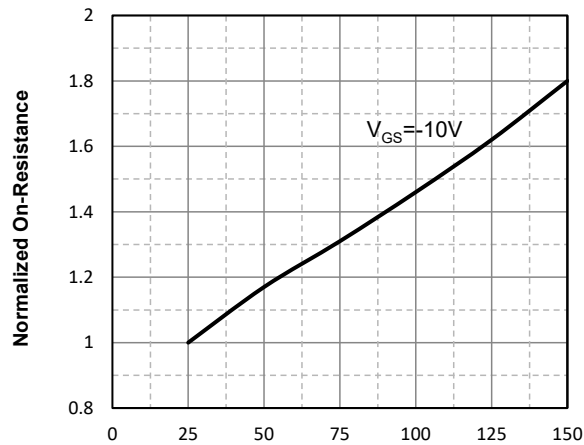


Fig3. Normalized On-Resistance Vs. Temperature

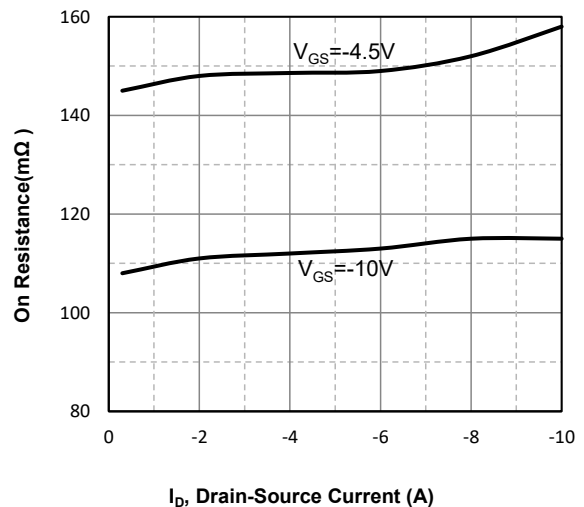


Fig4. On Resistance Vs. Drain-Source Current

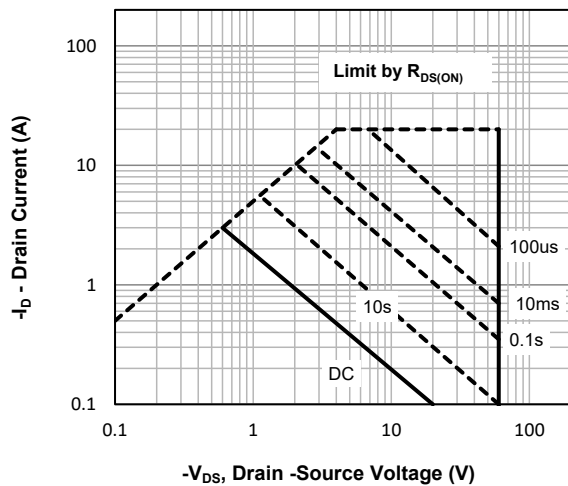


Fig5. Maximum Safe Operating Area

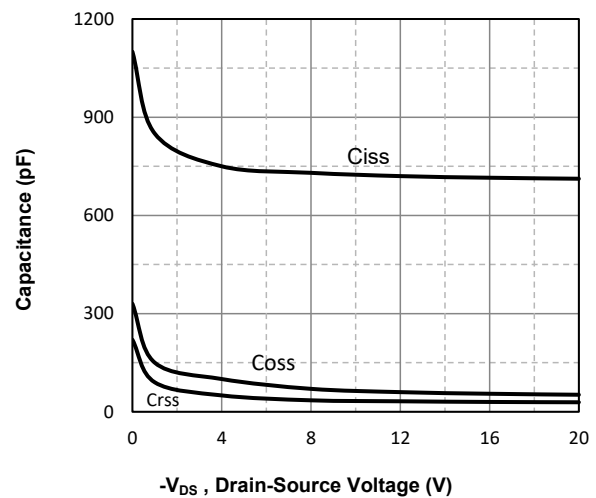
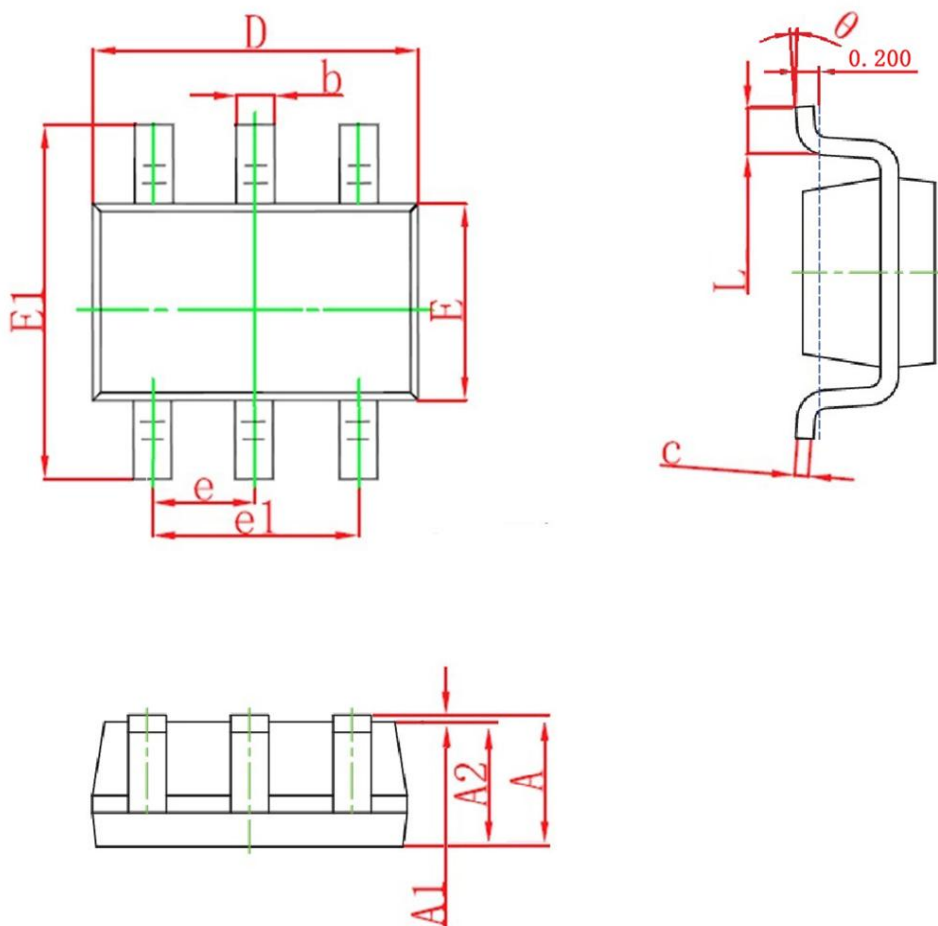


Fig6 Typical Capacitance Vs. Drain-Source Voltage

SOT-23-3L Package information



Symbol	Dimensions in Millimeters(mm)		Dimensions In Inches	
	Min	Max	Min	Max
A	1.050	1.250	0.042	0.050
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.042	0.046
b	0.300	0.500	0.012	0.020
c	0.100	0.200	0.004	0.008
D	2.820	3.020	0.112	0.120
E	1.500	1.700	0.060	0.068
E1	2.650	2.950	0.106	0.118
e	0.950TYP		0.037TYP	
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
θ	0°	8°	0°	8°